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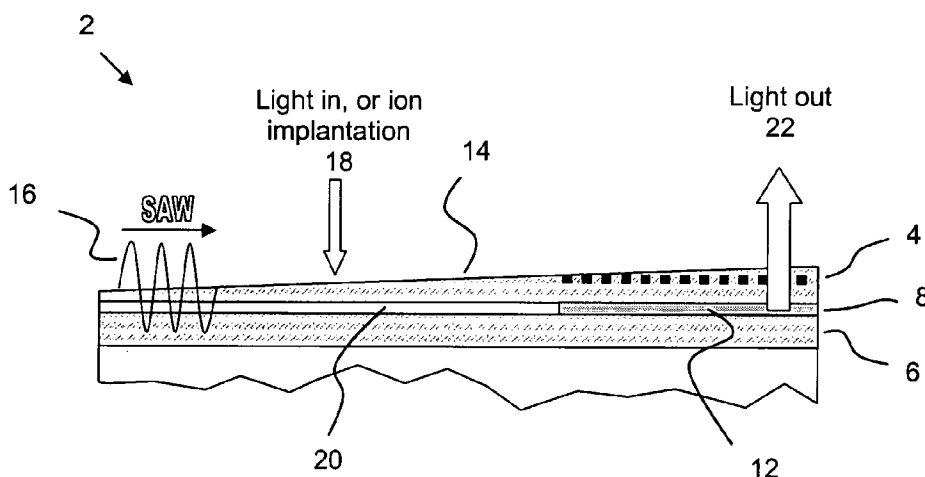
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(54) Title: METHOD FOR FABRICATING LATERAL SEMICONDUCTOR DEVICE



(57) Abstract: A lateral junction semiconductor device and method for fabricating the same comprising the steps of taking a semiconductor structure (2) having a stack formed by a plurality of layers of semiconductor material arranged in a series of substantially parallel planes, the semiconductor material within a first layer (4) having an excess of charge carriers of a first polarity at a first concentration, and selectively removing semiconductor material from the first layer (4) to a depth which varies along a first direction substantially parallel with the planes of the layers within the structure, so as to provide a gradation of the concentration of charge carriers of first polarity within an active layer (8) along the first direction. A photon source comprising said lateral junction semiconductor device.

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